



Brudnyi Pavel

PERSONAL INFORMATION

Address: 13/a Mokrushina Street, apt. 146, Tomsk, 634045, Russia

Telephone: mobile: +7-909-546-7555

Email: paul702600@gmail.com

Date of birth: 4th May 1994

Nationality: Russian

Marital status: single

Languages: Russian, English

EDUCATION

Tomsk State University (TSU)

- M.Sc in Radiophysics Sept. 2016 – June 2018
Department of Semiconductor Electronics
- B.Sc in Radiophysics Sept. 2012 – June 2016
Department of Semiconductor Electronics

National Taiwan University (NTU)

- Exchange student Sept. 2017 – Jan. 2018
Graduate Institute of Electrical
Engineering and Computer Science

WORK EXPERIENCE

Tomsk State University (TSU)

- Laboratory assistant in the scientific Sept. 2015 – Jan. 2018
center «Nanoelectronics»

- Engineer in the scientific center «Nanoelectronics»

Jan.2018 - Present

- Admittance spectroscopy
- Raman spectroscopy
- Automation of measuring equipment
- Atomic force microscope

Participation in scientific projects:

- Quantum-dimensional light-emitting diode heterostructure InGaN/GaN/Al₂O₃ in the visible wavelength range with short-period superlattices (17.07.2014 — 31.12.2016).
- Development of arsenide of gallium sensors for matrix X-ray detectors used in digital mammography and macromolecular crystallography (17.09.2014 — 31.12.2016).
- Research and development of manufacturing technology for ultrahigh-frequency monolithic integrated circuits based on InAlN/GaN heterostructures for space applications (26.09.2017 — present).

SPECIAL SKILLS

- Upper-Intermediate English
- Computer literacy (Microsoft Office...)
- Work with graphs and arrays of data (Origin, Mathcad)
- Basics of programming (LabVIEW, Pascal, C++)
- Certificate of first aid courses
- Driving License (Category A, B)

PUBLICATIONS

Brudnyi V.N., Bojko V.M., Kolin N.G., Kosobutsky A.V., Korulin A.V., Brudnyi P.A., Ermakov V.S. Neutron irradiation-induced modification of electrical and structural properties of GaN epilayers grown on Al₂O₃ (0001) substrate //Semiconductor Science and Technology. 2018. Vol. 33, № 9. P. 095011-1-095011-8.

Brudnyi V.N., Vilisova M.D., Velicovskiy L.E, Sim P.E., Brudnyi P.A.
Electrophysicheskie i fiziko-khimicheskie svoystva omicheskikh kontaktov dly soedineniy III-N //Izvestia Vyshish Uchebnykh Zavedeniy. Physica. 2018. Vol.61, №8.

Denis V. Grigoryev, Vadim A. Novikov, Pavel A. Brudnyi, Anna M. Bogatyreva, Victor F. Tarasenko, Michail A. Shulepov. The influence of pulsed volume nanosecond discharge in air at atmospheric pressure on the surface potential distribution of MIS-structures based on p-CdHgTe in the V-defect region // International Congress on Energy Fluxes and Radiation Effects: Abstracts. Tomsk: TPU Publishing House, 2016. P. 272.

MEMBERSHIPS

IEEE and IEEE Photonics Society